# Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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# MOS FIELD EFFECT TRANSISTOR NP160N04TDG

# SWITCHING N-CHANNEL POWER MOS FET

#### DESCRIPTION

The NP160N04TDG is N-channel MOS Field Effect Transistor designed for high current switching applications.

#### ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE		
NP160N04TDG-E1-AY Note		Tape 800 p/reel			
NP160N04TDG-E2-AY Note	04TDG-E2-AY Note Pure Sn (Tin)		TO-263-7pin (MP-25ZT) typ. 1.5 g		

Note Pb-free (This product does not contain Pb in the external electrode).

#### FEATURES

- Super low on-state resistance  $R_{DS(on)1} = 1.6 \text{ m}\Omega \text{ TYP.} / 2.0 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, \text{ ID} = 80 \text{ A})$  $R_{DS(on)2} = 2.2 \text{ m}\Omega \text{ TYP.} / 5.4 \text{ m}\Omega \text{ MAX.} (V_{GS} = 4.5 \text{ V}, \text{ ID} = 80 \text{ A})$
- High Current Rating ID(DC) = ±160 A
- Logic level drive type

#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	40	V
Gate to Source Voltage (VDs = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	D(DC)	±160	А
Drain Current (pulse) Note1	D(pulse)	±640	А
Total Power Dissipation (Tc = $25^{\circ}$ C)	PT1	220	W
Total Power Dissipation (T <sub>A</sub> = 25°C)	PT2	1.8	W
Channel Temperature	Tch	175	°C
Storage Temperature	Tstg	-55 to +175	°C
Single Avalanche Energy Note2	Eas	372	mJ
Repetitive Avalanche Current Note3	IAR	61	А
Repetitive Avalanche Energy Note3	Ear	372	mJ

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

- 2. Starting Tch = 25°C, VDD = 20 V, RG = 25  $\Omega,$  VGS = 20  $\rightarrow$  0 V, L = 100  $\mu H$
- 3. RG = 25  $\Omega$ , Tch(peak)  $\leq$  150°C

## THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	0.68	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W

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Document No. D18761EJ2V0DS00 (2nd edition) Date Published July 2007 NS CP(K) Printed in Japan

The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.



(TO-263-7pin)

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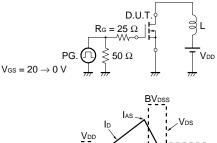
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V			1	μA
Gate Leakage Current	lgss	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±100	nA
Gate to Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 40 A	37	94		S
Drain to Source On-state Resistance <sup>Note</sup>	RDS(on)1	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 80 A		1.6	2.0	mΩ
	RDS(on)2	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 80 A		2.2	5.4	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = 25 V,		10500	15750	pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V,		980	1470	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		630	1140	pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = 20 V, I <sub>D</sub> = 80 A,		35	80	ns
Rise Time	tr	V <sub>GS</sub> = 10 V,		55	140	ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 0 Ω		107	220	ns
Fall Time	tr			17	50	ns
Total Gate Charge <sup>Note</sup>	QG	V <sub>DD</sub> = 32 V,		180	270	nC
Gate to Source Charge	QGS	V <sub>GS</sub> = 10 V,		30		nC
Gate to Drain Charge	Qgd	I <sub>D</sub> = 160 A		57		nC
Body Diode Forward Voltage Note	VF(S-D)	I⊧ = 160 A, V <sub>GS</sub> = 0 V		0.9	1.5	V
Reverse Recovery Time	trr	I⊧ = 160 A, V <sub>GS</sub> = 0 V,		49		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ <i>µ</i> s		60		nC
	Zero Gate Voltage Drain Current Gate Leakage Current Gate to Source Threshold Voltage Forward Transfer Admittance <sup>Note</sup> Drain to Source On-state Resistance <sup>Note</sup> Input Capacitance Output Capacitance Reverse Transfer Capacitance Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time Total Gate Charge <sup>Note</sup> Gate to Source Charge Gate to Drain Charge Body Diode Forward Voltage <sup>Note</sup> Reverse Recovery Time	Zero Gate Voltage Drain Current IDDSS   Gate Leakage Current IGSS   Gate to Source Threshold Voltage VGS(th)   Forward Transfer Admittance Note  yfs    Drain to Source On-state Resistance Note RDS(on)1   Input Capacitance Ciss   Output Capacitance Coss   Reverse Transfer Capacitance Crss   Turn-on Delay Time ta(on)   Rise Time tr   Turn-off Delay Time ta(off)   Fall Time QG   Gate to Source Charge QG   Gate to Drain Charge VGS   Body Diode Forward Voltage VF(S-D)   Reverse Recovery Time tr	Zero Gate Voltage Drain CurrentIbss $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$ Gate Leakage CurrentIass $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ Gate to Source Threshold Voltage $V_{GS}(th)$ $V_{DS} = V_{GS}, I_D = 250 \mu$ AForward Transfer Admittance Note $ y_{15} $ $V_{DS} = 5 \text{ V}, I_D = 40 \text{ A}$ Drain to Source On-state Resistance Note $R_{DS(on)1}$ $V_{GS} = 10 \text{ V}, I_D = 80 \text{ A}$ Input Capacitance $C_{ISS}$ $V_{DS} = 25 \text{ V},$ Output Capacitance $C_{OSS}$ $V_{DS} = 25 \text{ V},$ Output Capacitance $C_{OSS}$ $V_{DS} = 0 \text{ V},$ Reverse Transfer Capacitance $C_{rss}$ $f = 1 \text{ MHz}$ Turn-on Delay Time $t_{d(on)}$ $V_{DD} = 20 \text{ V}, I_D = 80 \text{ A},$ Rise Time $t_r$ $V_{CS} = 10 \text{ V},$ Turn-off Delay Time $t_{a(off)}$ $R_G = 0 \Omega$ Fall Time $t_r$ $V_{CS} = 10 \text{ V},$ Gate to Source Charge $Q_{GS}$ $V_{DD} = 32 \text{ V},$ Gate to Drain Charge $Q_{GD}$ $I_D = 160 \text{ A}$ Body Diode Forward Voltage Note $V_{F(S-D)}$ $I_F = 160 \text{ A}, V_{GS} = 0 \text{ V},$	Zero Gate Voltage Drain CurrentIossVos = 40 V, Vos = 0 VGate Leakage CurrentIossVos = $\pm 20$ V, Vos = 0 V1Gate to Source Threshold VoltageVos (Vos = Vos, Ib = $250 \mu$ A1.5Forward Transfer Admittance NoteI yrs IVos = 5 V, Ib = $40$ A37Drain to Source On-state ResistanceRbs(on)1Vos = 10 V, Ib = $80$ A37Input CapacitanceCissVos = $4.5$ V, Ib = $80$ A1Input CapacitanceCissVos = $4.5$ V, Ib = $80$ A1Input CapacitanceCossVos = $25$ V,1Output CapacitanceCossVos = $0$ V,1Turn-on Delay Timeta(on)Vob = $20$ V, Ib = $80$ A,1Turn-off Delay Timeta(on)Vob = $20$ V, Ib = $80$ A,1Fall TimetrVob = $20$ V, Ib = $80$ A,1Total Gate ChargeQaVob = $32$ V,1Gate to Source ChargeQaVob = $32$ V,1Gate to Drain ChargeQaVob = $10$ V,1Body Diode Forward VoltageVoteIr = $160$ A, Vos = $0$ V,1Reverse Recovery TimetrIr = $160$ A, Vos = $0$ V,1	Zero Gate Voltage Drain CurrentIossVos = 40 V, Vos = 0 VImage: Constraint of the second state of the s	Zero Gate Voltage Drain Current   Ioss   Vos = 40 V, Vos = 0 V   Image: Mode Set Set Set Set Set Set Set Set Set Se

## ELECTRICAL CHARACTERISTICS (TA = 25°C)

Note Pulsed test

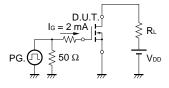
#### TEST CIRCUIT 1 AVALANCHE CAPABILITY

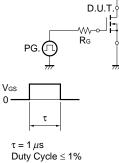
#### **TEST CIRCUIT 2 SWITCHING TIME**

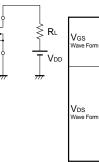


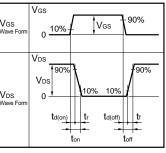
Starting T<sub>ch</sub>

#### **TEST CIRCUIT 3 GATE CHARGE**

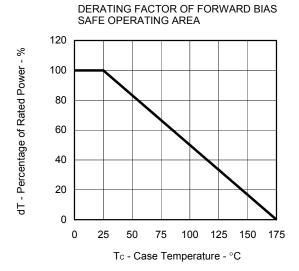




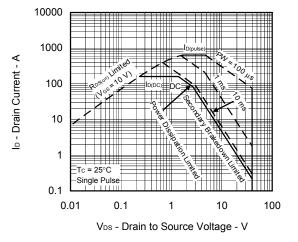


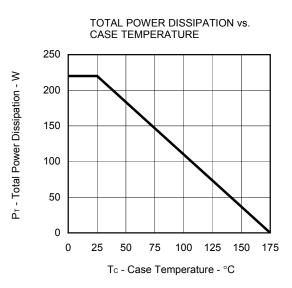


# TYPICAL CHARACTERISTICS (TA = 25°C)

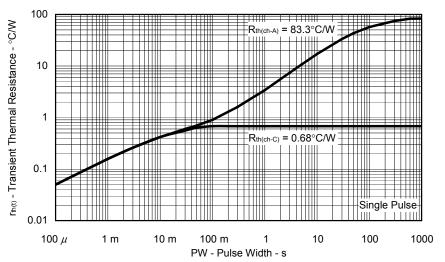




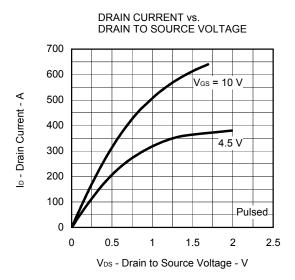




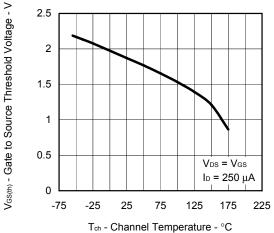
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

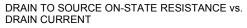


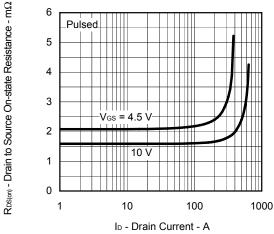
Data Sheet D18761EJ2V0DS



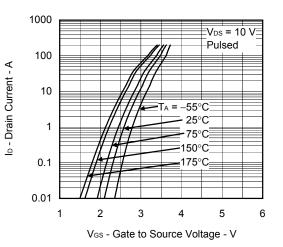




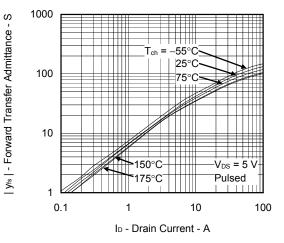


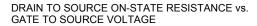


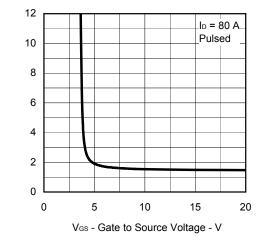
FORWARD TRANSFER CHARACTERISTICS



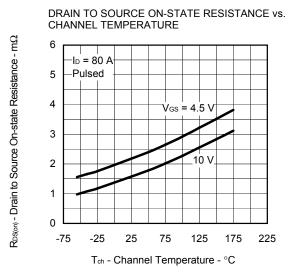
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



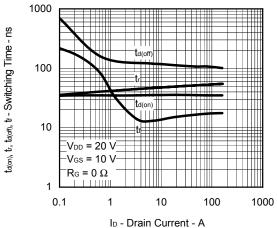


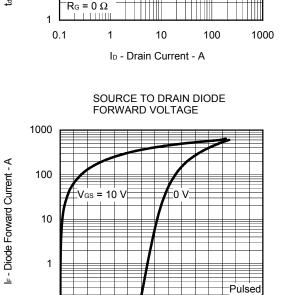


 $R_{DS(cn)}$  - Drain to Source On-state Resistance -  $m\Omega$ 









V<sub>F(S-D)</sub> - Source to Drain Voltage - V

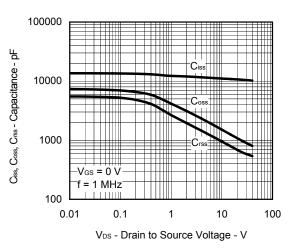
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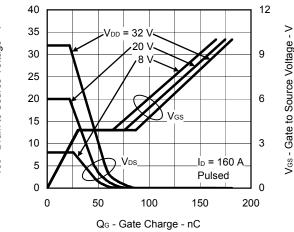
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<R> CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

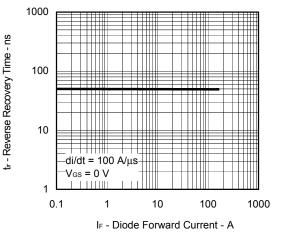


DYNAMIC INPUT/OUTPUT CHARACTERISTICS





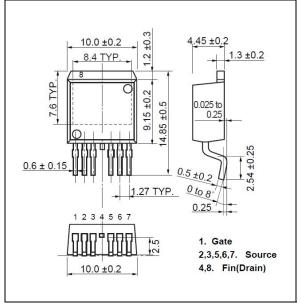
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



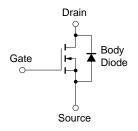
1.5

# PACKAGE DRAWING (Unit: mm)

#### TO-263-7pin (MP-25ZT)



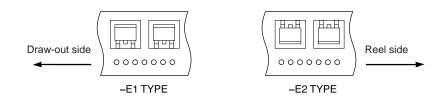
# EQUIVALENT CIRCUIT



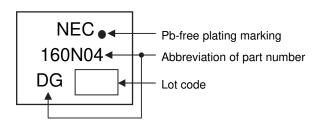
**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

#### TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



#### MARKING INFORMATION



#### **RECOMMENDED SOLDERING CONDITIONS**

The NP160N04TDG should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol	
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below		
	Time at maximum temperature: 10 seconds or less		
	Time of temperature higher than 220°C: 60 seconds or less	IR60-00-3	
	Preheating time at 160 to 180°C: 60 to 120 seconds		
	Maximum number of reflow processes: 3 times		
	Maximum chlorine content of rosin flux (percentage mass): 0.2% or less		
Partial heating	Maximum temperature (Pin temperature): 350°C or below		
	Time (per side of the device): 3 seconds or less	P350	
	Maximum chlorine content of rosin flux: 0.2% (wt.) or less		

Caution Do not use different soldering methods together (except for partial heating).

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